Course Name:B.Tech. (ECE), Semester:3rd (November-December, 2023)

Subject Code: BEC 201

Time :3 Hours

Maximum Marks :60

Note:Q. 1 is compulsory. Attempt one question each from the Units I, II, III & IV.

description of the last	Q. 1 is compulsory. Attempt one question each from the Units 1, 11,	
Q1		2.5*8=20
	(a) Differentiate among types of capacitances present in a Si diode when it biased and forward biased. Comment on the change in capacitance increase in reverse in the Si diode.	t is reverse level with
	(b) Give principal of 7. It is its usage as voltage regulator.	
	(d) Use of temperature variation of open v-I characteristic curve.	
	vinat is pinch-off voltage? How it is affected by variation as	
	(f) Give advantages of R-C coupled transistor amplifier over transformed transistor amplifier.	
	(g) Describe the phenomenon "channel length modulation" versus "b modulation".	pase width
	(h) Why the terminology field effect appropriate for JFET transistor and when high input impedance and effectively zero gate current?	ny JFET has
	UNIT-I	(10)
Q2	Determine the output v_o of the network given below in Fig. 1 if the input waveform v_i (given in Fig. 2) is applied to this network.	(10)
	$C = 1 \mu F$	
	+	
	ν _i	
	Fig. 1	
	f = 1000 Hz	
	$-20 \begin{array}{ c c c c c c c c c c c c c c c c c c c$	
	Fig. 2	
Q3	Identify the types of biasing techniques applied in circuits given below in Fig. and Fig. 4. Compare both these techniques for the thermal stability provided to circuit in terms of Stability 'S' factor.	3 (10)

